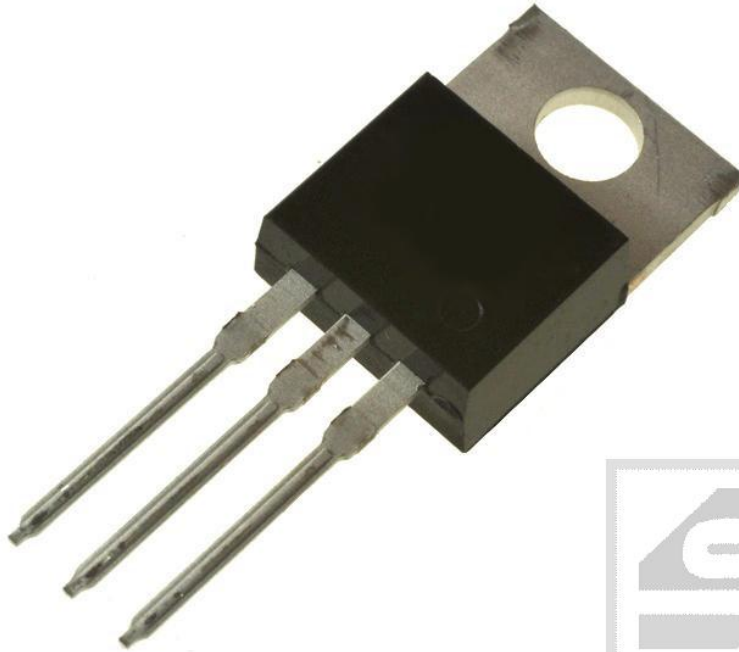




ROBERT STĘPIEŃ
HURTOWNIA CZĘŚCI ELEKTRONICZNYCH
podzespoly-elektroniczne.pl

STP65NF06;ST;TO220;60A;60V; 11.5mR;110W;RoHS



Dane techniczne:

Nazwa: STP65NF06

Typ tranzystora: unipolarny

Kierunek przewodnictwa: N-MOSFET

Prąd kolektora: 60A

Napięcie kolektor-emiter: 60V

Moc: 110W

Montaż: przewlekany(THT)

Obudowa: TO220

Producent: ST

www.podzespoly-elektroniczne.pl

Robert Stępień Hurtownia Części Elektronicznych; Adres: ul. Wolumen 2, pawilon 71; 01-912 Warszawa; tel.: 601 296 402 / sklep@podzespoly-elektroniczne.pl



STD65NF06 STP65NF06

N-channel 60V - 11.5mΩ - 60A - DPAK/TO-220
STripFET™ II Power MOSFET

General features

| Type | V _{DSS} | R _{DS(on)} | I _D |
|-----------|------------------|---------------------|----------------|
| STD65NF06 | 60V | <14mΩ | 60A |
| STP65NF06 | 60V | <14mΩ | 60A |

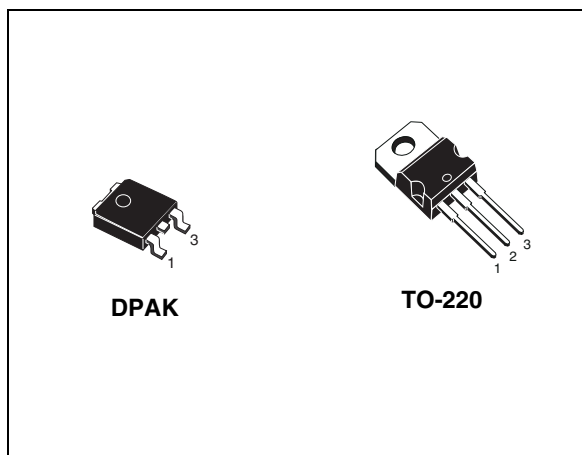
- Standard level gate drive
- 100% avalanche tested

Description

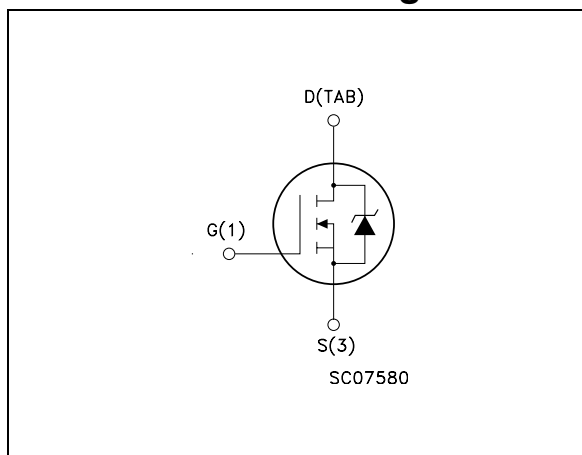
This Power MOSFET is the latest development of STMicroelectronics unique “single feature size”™ strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

Applications

- Switching application



Internal schematic diagram



Order codes

| Part number | Marking | Package | Packaging |
|-------------|---------|---------|-------------|
| STD65NF06 | D65NF06 | DPAK | Tape & reel |
| STP65NF06 | P65NF06 | TO-220 | Tube |

Contents

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1 Electrical ratings

Table 1. Absolute maximum ratings

| Symbol | Parameter | Value | Unit |
|----------------|---|------------|---------------------|
| V_{DS} | Drain-source voltage ($V_{GS} = 0$) | 60 | V |
| V_{GS} | Gate- source voltage | ± 20 | V |
| I_D | Drain current (continuous) at $T_C = 25^\circ\text{C}$ | 60 | A |
| I_D | Drain current (continuous) at $T_C = 100^\circ\text{C}$ | 42 | A |
| $I_{DM}^{(1)}$ | Drain current (pulsed) | 240 | A |
| P_{tot} | Total dissipation at $T_C = 25^\circ\text{C}$ | 110 | W |
| | Derating Factor | 0.73 | W/ $^\circ\text{C}$ |
| $dv/dt^{(2)}$ | Peak diode recovery voltage slope | 10 | V/ns |
| $E_{AS}^{(3)}$ | Single pulse avalanche energy | 390 | mJ |
| T_{stg} | Storage temperature | -55 to 175 | $^\circ\text{C}$ |
| T_j | Max. operating junction temperature | | |

1. Pulse width limited by safe operating area.
2. $I_{SD} \leq 60\text{A}$, $di/dt \leq 300\text{A}/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$, $T_j \leq T_{JMAX}$
3. Starting $T_j = 25^\circ\text{C}$, $I_D = 30\text{A}$, $V_{DD} = 40\text{V}$

Table 2. Thermal data

| Symbol | Parameter | TO-220 | DPAK | Unit |
|---------------------|---|--------|------|---------------------------|
| $R_{thj-case}$ | Thermal resistance junction-case max | 1.36 | | $^\circ\text{C}/\text{W}$ |
| $R_{thj-amb}$ | Thermal resistance junction-ambient max | 62.5 | -- | $^\circ\text{C}/\text{W}$ |
| $R_{thj-pcb}^{(1)}$ | Thermal resistance junction-pcb max | -- | 50 | $^\circ\text{C}/\text{W}$ |
| T_l | Maximum lead temperature for soldering purpose (for 10sec. 1.6mm from case) | 300 | -- | $^\circ\text{C}/\text{W}$ |

1. When mounted on FR-4 of 1 inch², 2 oz Cu

2 Electrical characteristics

($T_{CASE}=25^{\circ}C$ unless otherwise specified)

Table 3. On/off states

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|---------------|--|---|------|------|-----------|--------------------|
| $V_{(BR)DSS}$ | Drain-source breakdown voltage | $I_D = 250\mu A, V_{GS} = 0$ | 60 | | | V |
| I_{DSS} | Zero gate voltage drain current ($V_{GS} = 0$) | $V_{DS} = \text{Max rating}$ $V_{DS} = \text{Max rating, @ } 125^{\circ}C$ | | | 1 10 | μA μA |
| I_{GSS} | Gate-body leakage current ($V_{DS} = 0$) | $V_{GS} = \pm 20V$ | | | ± 100 | nA |
| $V_{GS(th)}$ | Gate threshold voltage | $V_{DS} = V_{GS}, I_D = 250\mu A$ | 2 | | 4 | V |
| $R_{DS(on)}$ | Static drain-source on resistance | $V_{GS} = 10V, I_D = 30A$ | | 11.5 | 14 | m Ω |

Table 4. Dynamic

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|---|---|---|------|----------------------|------|----------------------|
| $g_{fs}^{(1)}$ | Forward transconductance | $V_{DS} = 25V, I_D = 30A$ | | 50 | | S |
| C_{iss} C_{oss} C_{rss} | Input capacitance Output capacitance Reverse transfer capacitance | $V_{DS} = 25V, f = 1MHz,$ $V_{GS} = 0$ | | 1700 400 135 | | pF pF pF |
| $t_{d(on)}$ t_r $t_{d(off)}$ t_f | Turn-on delay time Rise time Turn-off delay time Fall time | $V_{DD} = 30V, I_D = 30A$ $R_G = 4.7\Omega, V_{GS} = 10V$ (see Figure 12) | | 15 60 40 16 | | ns ns ns ns |
| Q_g Q_{gs} Q_{gd} | Total gate charge Gate-source charge Gate-drain charge | $V_{DD} = 30V, I_D = 60A,$ $V_{GS} = 10V, R_G = 4.7\Omega$ (see Figure 13) | | 54 10 20 | 75 | nC nC nC |

1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.

Table 5. Source drain diode

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|-----------------------------------|--|--|------|------------------|-----------|---------------|
| I_{SD} $I_{SDM}^{(1)}$ | Source-drain current Source-drain current (pulsed) | | | | 60 240 | A A |
| $V_{SD}^{(2)}$ | Forward on voltage | $I_{SD} = 60A, V_{GS} = 0$ | | | 1.5 | V |
| t_{rr} Q_{rr} I_{RRM} | Reverse recovery time Reverse recovery charge Reverse recovery current | $I_{SD} = 60A, di/dt = 100A/\mu s,$ $V_{DD} = 25V, T_j = 150^\circ C$ (see Figure 14) | | 70 150 4.4 | | ns nC A |

1. Pulse width limited by safe operating area.
2. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

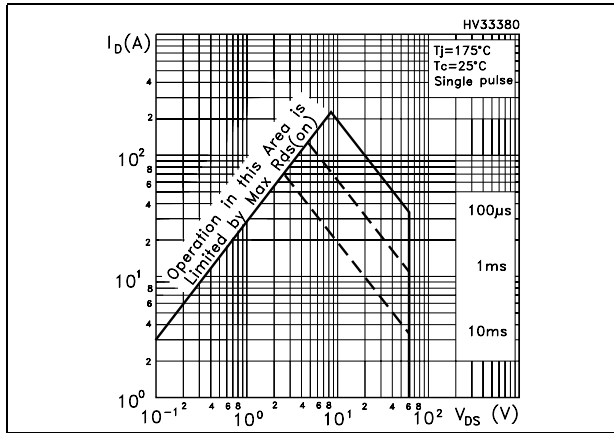


Figure 2. Thermal impedance

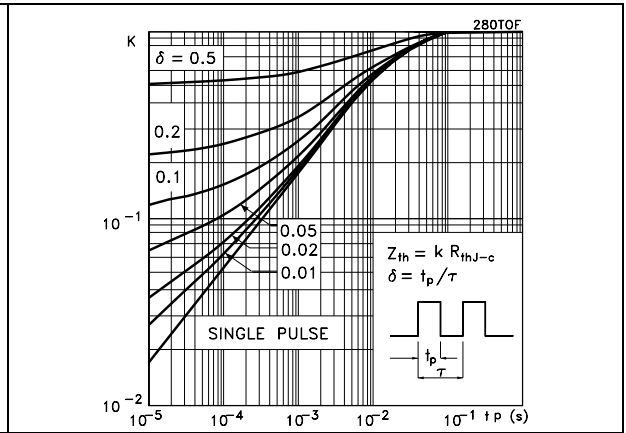


Figure 3. Output characteristics

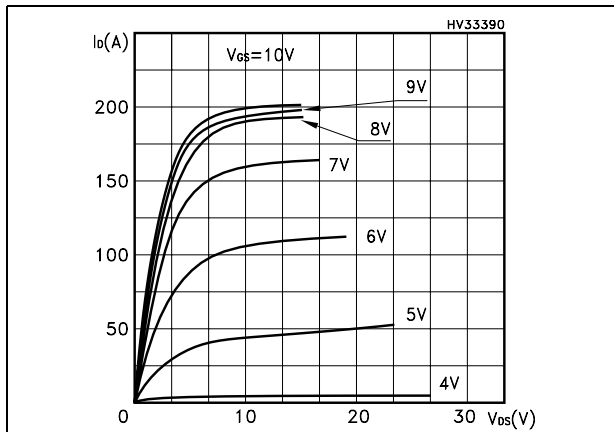


Figure 4. Transfer characteristics

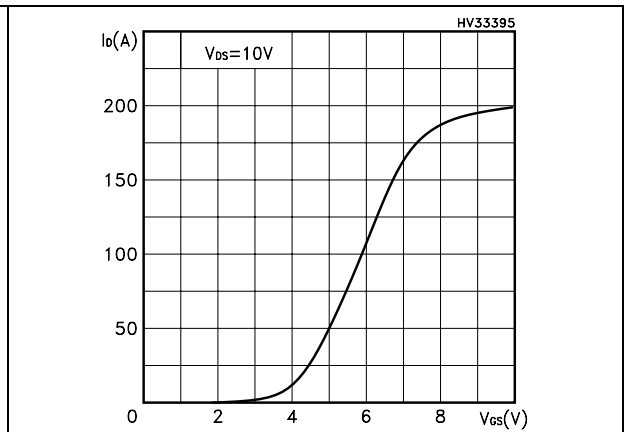


Figure 5. Normalized breakdown voltage temperature

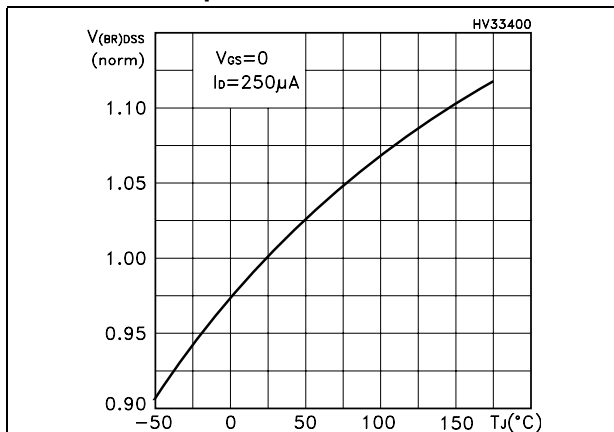


Figure 6. Static drain-source on resistance

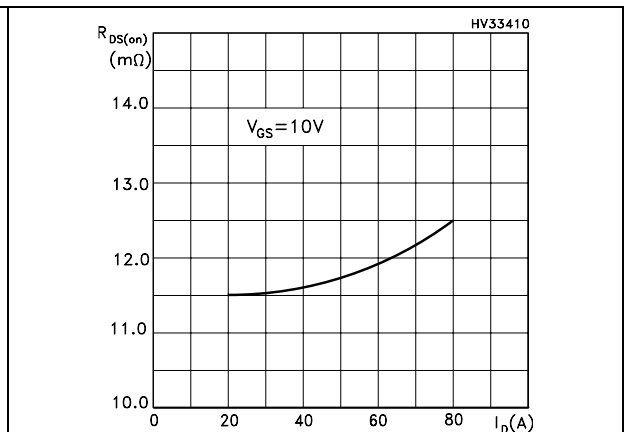


Figure 7. Gate charge vs gate-source voltage Figure 8. Capacitance variations

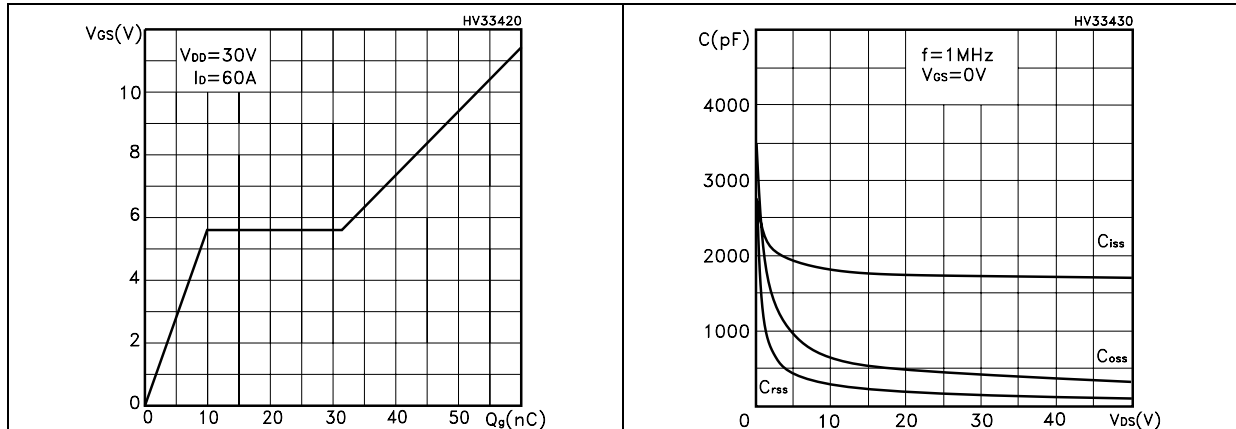


Figure 9. Normalized gate threshold voltage vs temperature Figure 10. Normalized on resistance vs temperature

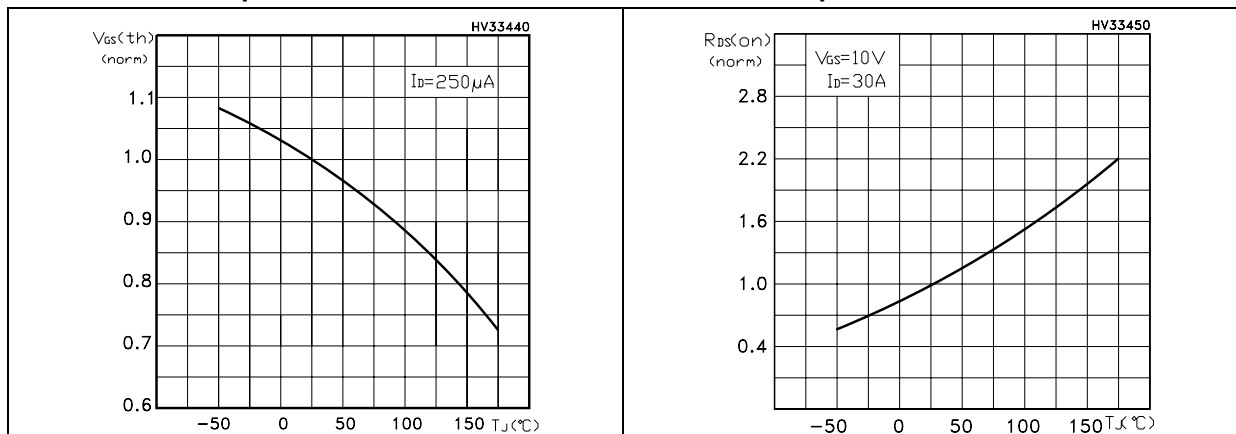
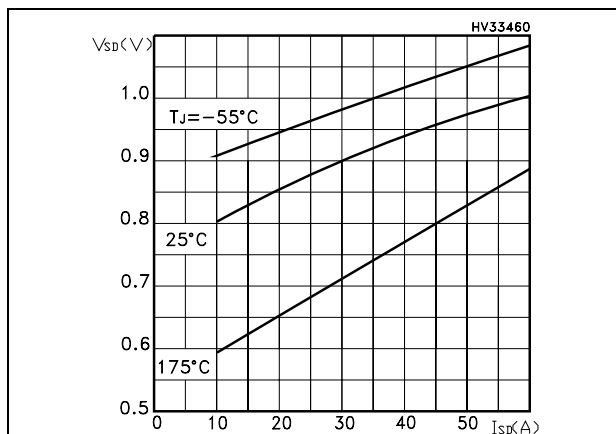


Figure 11. Source-drain diode forward characteristics



3 Test circuit

Figure 12. Switching times test circuit for resistive load

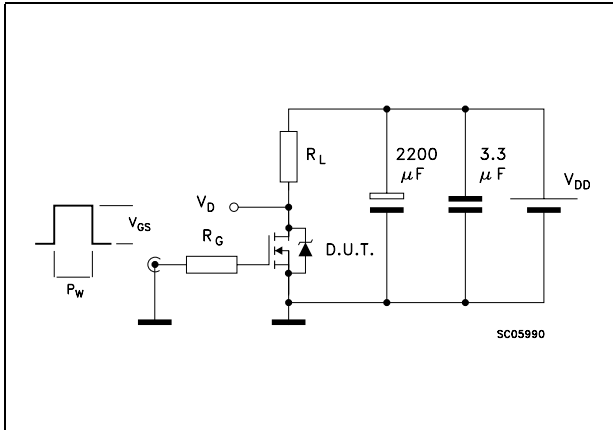


Figure 13. Gate charge test circuit

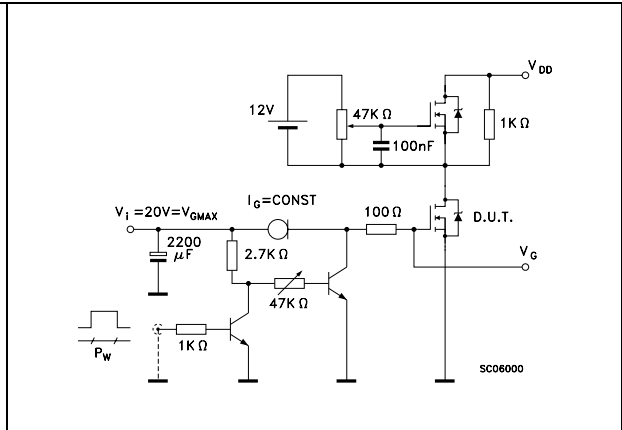


Figure 14. Test circuit for inductive load switching and diode recovery times

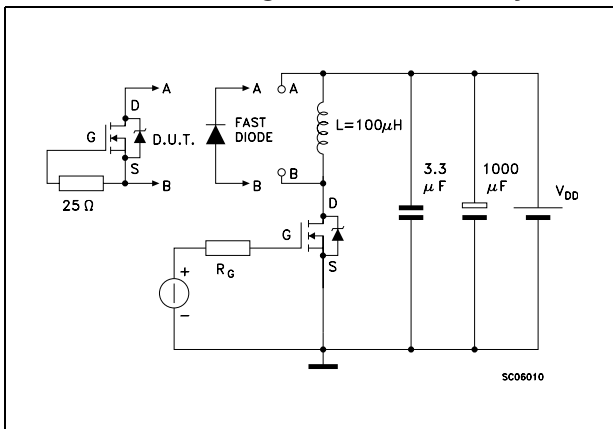


Figure 15. Unclamped Inductive load test circuit

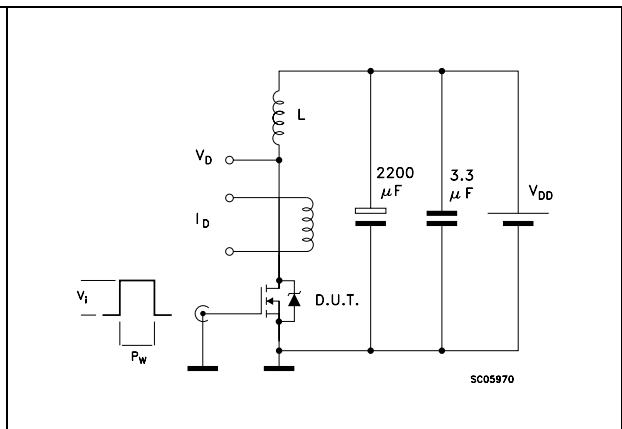


Figure 16. Unclamped inductive waveform

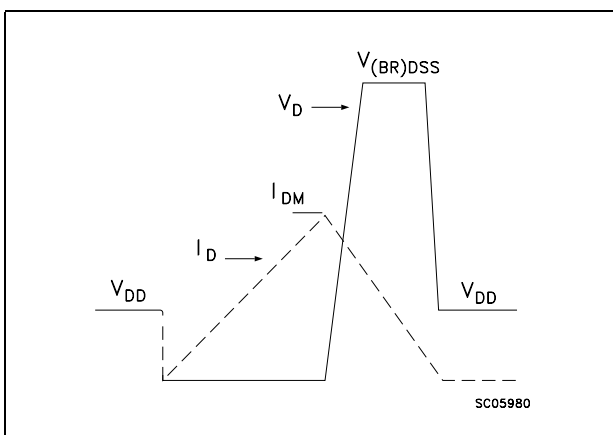
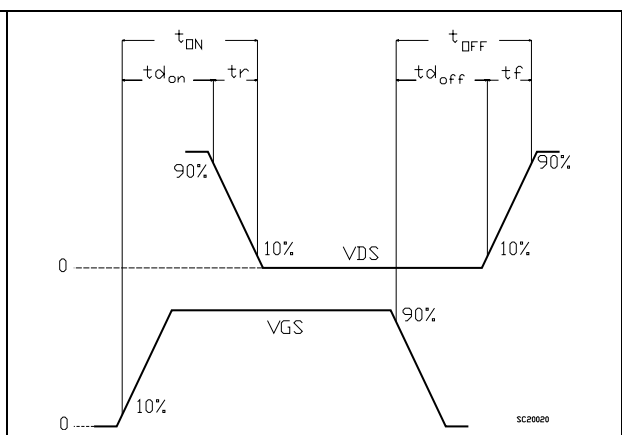


Figure 17. Switching time waveform

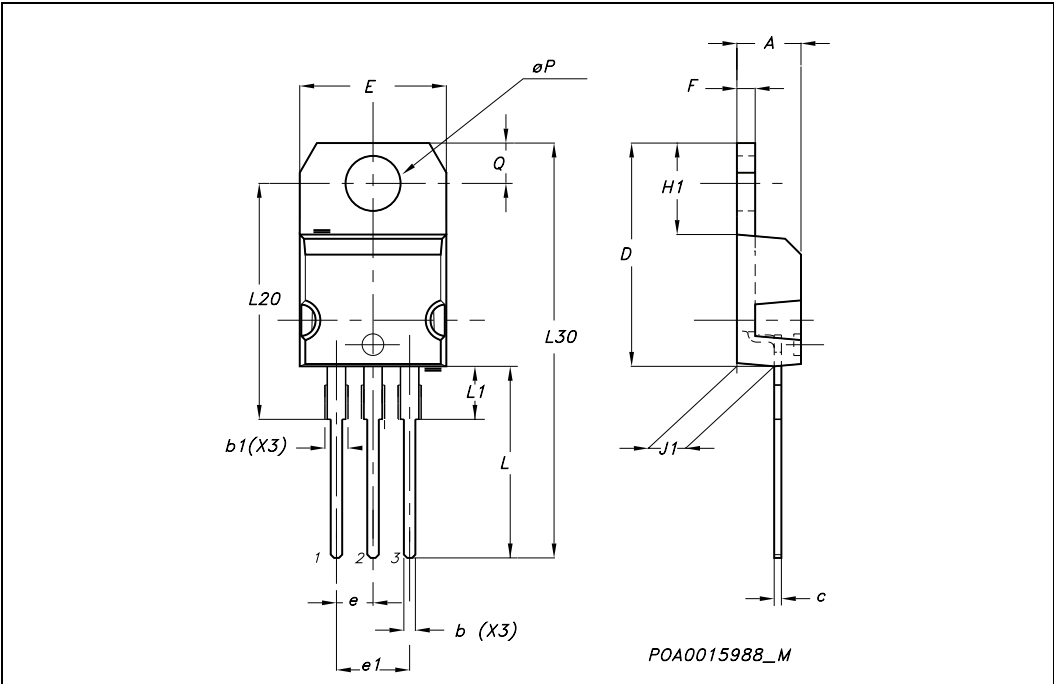


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at : www.st.com

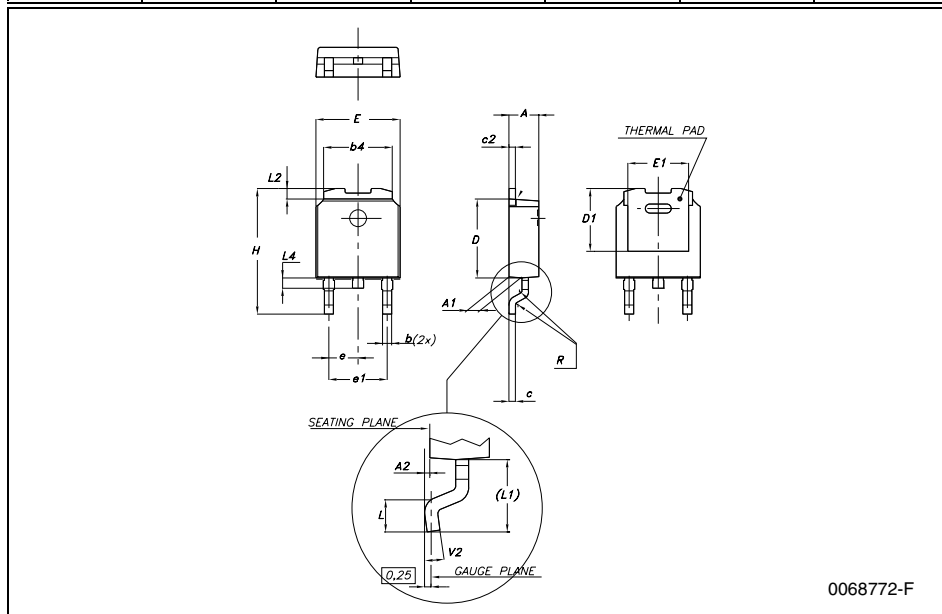
TO-220 MECHANICAL DATA

| DIM. | mm. | | | inch | | |
|------|-------|-------|-------|-------|-------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| A | 4.40 | | 4.60 | 0.173 | | 0.181 |
| b | 0.61 | | 0.88 | 0.024 | | 0.034 |
| b1 | 1.15 | | 1.70 | 0.045 | | 0.066 |
| c | 0.49 | | 0.70 | 0.019 | | 0.027 |
| D | 15.25 | | 15.75 | 0.60 | | 0.620 |
| E | 10 | | 10.40 | 0.393 | | 0.409 |
| e | 2.40 | | 2.70 | 0.094 | | 0.106 |
| e1 | 4.95 | | 5.15 | 0.194 | | 0.202 |
| F | 1.23 | | 1.32 | 0.048 | | 0.052 |
| H1 | 6.20 | | 6.60 | 0.244 | | 0.256 |
| J1 | 2.40 | | 2.72 | 0.094 | | 0.107 |
| L | 13 | | 14 | 0.511 | | 0.551 |
| L1 | 3.50 | | 3.93 | 0.137 | | 0.154 |
| L20 | | 16.40 | | | 0.645 | |
| L30 | | 28.90 | | | 1.137 | |
| øP | 3.75 | | 3.85 | 0.147 | | 0.151 |
| Q | 2.65 | | 2.95 | 0.104 | | 0.116 |



DPAK MECHANICAL DATA

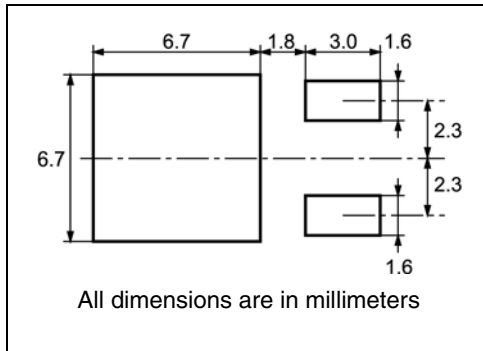
| DIM. | mm. | | | inch | | |
|------|------|------|------|-------|-------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| A | 2.2 | | 2.4 | 0.086 | | 0.094 |
| A1 | 0.9 | | 1.1 | 0.035 | | 0.043 |
| A2 | 0.03 | | 0.23 | 0.001 | | 0.009 |
| B | 0.64 | | 0.9 | 0.025 | | 0.035 |
| b4 | 5.2 | | 5.4 | 0.204 | | 0.212 |
| C | 0.45 | | 0.6 | 0.017 | | 0.023 |
| C2 | 0.48 | | 0.6 | 0.019 | | 0.023 |
| D | 6 | | 6.2 | 0.236 | | 0.244 |
| D1 | | 5.1 | | | 0.200 | |
| E | 6.4 | | 6.6 | 0.252 | | 0.260 |
| E1 | | 4.7 | | | 0.185 | |
| e | | 2.28 | | | 0.090 | |
| e1 | 4.4 | | 4.6 | 0.173 | | 0.181 |
| H | 9.35 | | 10.1 | 0.368 | | 0.397 |
| L | 1 | | | 0.039 | | |
| (L1) | | 2.8 | | | 0.110 | |
| L2 | | 0.8 | | | 0.031 | |
| L4 | 0.6 | | 1 | 0.023 | | 0.039 |
| R | | 0.2 | | | 0.008 | |
| V2 | 0° | | 8° | 0° | | 8° |



0068772-F

5 Packing mechanical data

DPAK FOOTPRINT



TAPE AND REEL SHIPMENT

| DIM. | mm | | inch | |
|------|------|------|-------|--------|
| | MIN. | MAX. | MIN. | MAX. |
| A | | 330 | | 12.992 |
| B | 1.5 | | 0.059 | |
| C | 12.8 | 13.2 | 0.504 | 0.520 |
| D | 20.2 | | 0.795 | |
| G | 16.4 | 18.4 | 0.645 | 0.724 |
| N | 50 | | 1.968 | |
| T | | 22.4 | | 0.881 |

| DIM. | mm | | inch | |
|------|------|------|-------|-------|
| | MIN. | MAX. | MIN. | MAX. |
| A0 | 6.8 | 7 | 0.267 | 0.275 |
| B0 | 10.4 | 10.6 | 0.409 | 0.417 |
| B1 | | 12.1 | | 0.476 |
| D | 1.5 | 1.6 | 0.059 | 0.063 |
| D1 | 1.5 | | 0.059 | |
| E | 1.65 | 1.85 | 0.065 | 0.073 |
| F | 7.4 | 7.6 | 0.291 | 0.299 |
| K0 | 2.55 | 2.75 | 0.100 | 0.108 |
| P0 | 3.9 | 4.1 | 0.153 | 0.161 |
| P1 | 7.9 | 8.1 | 0.311 | 0.319 |
| P2 | 1.9 | 2.1 | 0.075 | 0.082 |
| R | 40 | | 1.574 | |
| W | 15.7 | 16.3 | 0.618 | 0.641 |

6 Revision history

Table 6. Revision history

| Date | Revision | Changes |
|-------------|----------|---------------|
| 24-Jul-2006 | 1 | First release |

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